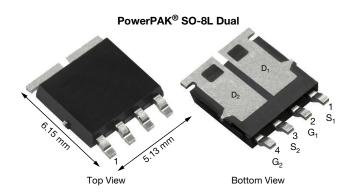


Vishay Siliconix

Automotive Dual N-Channel 40 V (D-S) 175 °C MOSFET



PRODUCT SUMMARY					
V _{DS} (V)	40				
$R_{DS(on)}(\Omega)$ at $V_{GS} = 10 \text{ V}$	0.0073				
$R_{DS(on)}(\Omega)$ at $V_{GS} = 4.5 \text{ V}$	0.0102				
I _D (A) per leg	30				
Configuration	Dual				
Package	PowerPAK SO-8L				

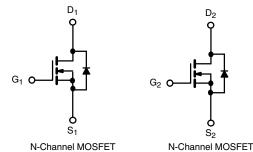
FEATURES

- TrenchFET® power MOSFET
- AEC-Q101 qualified
- 100 % R_q and UIS tested
- Material categorization: for definitions of compliance please see www.vishav.com/doc?99912





ROHS COMPLIANT HALOGEN FREE



PARAMETER		SYMBOL	LIMIT	UNIT	
Drain-source voltage		V _{DS}	40	V	
Gate-source voltage		V _{GS}	± 20		
Continuous drain current	T _C = 25 °C ^a	1	30		
	T _C = 125 °C	I _D	26		
Continuous source current (diode conduct	ion) ^a	I _S	25	Α	
Pulsed drain current ^b		I _{DM}	120		
Single pulse avalanche current		I _{AS}	19		
Single pulse avalanche energy	L = 0.1 mH	E _{AS}	18	mJ	
Maximum power dissipation ^b	T _C = 25 °C	Р	27	10/	
	T _C = 125 °C	°C P _D 9		W	
Operating junction and storage temperature range		T _J , T _{stg}	-55 to +175	00	
Soldering recommendations (peak temperature) d, e			260	°C	

THERMAL RESISTANCE RATINGS				
PARAMETER		SYMBOL	LIMIT	UNIT
Junction-to-ambient	PCB mount c	R_{thJA}	85	°C/W
Junction-to-case (drain)		R_{thJC}	5.5	C/VV

Notes

- a. Package limited
- b. Pulse test; pulse width \leq 300 μ s, duty cycle \leq 2 %
- c. When mounted on 1" square PCB (FR4 material)
- d. See solder profile (www.vishay.com/doc?73257). The PowerPAK SO-8L is a leadless package. The end of the lead terminal is exposed copper (not plated) as a result of the singulation process in manufacturing. A solder fillet at the exposed copper tip cannot be guaranteed and is not required to ensure adequate bottom side solder interconnection
- e. Rework conditions: manual soldering with a soldering iron is not recommended for leadless components

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PARAMETER	SYMBOL	TES	T CONDITIONS	MIN.	TYP.	MAX.	UNIT	
Static								
Drain-source breakdown voltage	V _{DS}	$V_{GS} = 0 \text{ V}, I_D = 250 \mu\text{A}$		40	-	-	V	
Gate-source threshold voltage	V _{GS(th)}	V _{DS} =	· V _{GS} , I _D = 250 μA	1.5	2.0	2.5	v	
Gate-source leakage	I _{GSS}	V _{DS} =	0 V, V _{GS} = ± 20 V	-	-	± 100	nA	
		$V_{GS} = 0 V$	V _{DS} = 40 V	-	-	1		
Zero gate voltage drain current	I _{DSS}	V _{GS} = 0 V	V _{DS} = 40 V, T _J = 125 °C	-	-	50	μΑ	
		V _{GS} = 0 V	V _{DS} = 40 V, T _J = 175 °C	-	-	150		
On-state drain current ^a	I _{D(on)}	V _{GS} = 10 V	$V_{DS} \ge 5 V$	15	-	-	Α	
	_	V _{GS} = 10 V	I _D = 7 A	-	0.0059	0.0073	Ω	
Duning and the project of the second		V _{GS} = 4.5 V	I _D = 5 A	-	0.0082	0.0102		
Drain-source on-state resistance ^a	R _{DS(on)}	V _{GS} = 10 V	I _D = 7 A, T _J = 125 °C	-	-	0.0106		
		V _{GS} = 10 V	I _D = 7 A, T _J = 175 °C	'n	-	0.0125		
Forward transconductance b	9 _{fs}	V_{DS}	= 15 V, I _D = 7 A	-	47	-	S	
Dynamic ^b								
Input capacitance	C _{iss}			-	1246	1745		
Output capacitance	C _{oss}	V _{GS} = 0 V	V _{DS} = 25 V, f = 1 MHz	-	345	483	рF	
Reverse transfer capacitance	C _{rss}	1		-	31	44		
Total gate charge ^c	Qg			'n	24	36		
Gate-source charge ^c	Q _{gs}	V _{GS} = 10 V	$V_{DS} = 20 \text{ V}, I_{D} = 11.3 \text{ A}$	-	5	-	nC	
Gate-drain charge ^c	Q _{gd}	1		-	5	-		
Gate resistance	R _g		f = 1 MHz	1.4	2.8	4.2	Ω	
Turn-on delay time ^c	t _{d(on)}	V_{DD} = 20 V, R_L = 20 Ω $I_D \cong$ 1 A, V_{GEN} = 10 V, R_g = 1 Ω		-	10	20	ns	
Rise time ^c	t _r			-	4	10		
Turn-off delay time ^c	t _{d(off)}			-	25	50		
Fall time ^c	t _f			-	21	35		
Source-Drain Diode Ratings and Charact	eristics b							
Pulsed current ^a	I _{SM}				-	120	А	
Forward voltage	V _{SD}	I _F = 7 A, V _{GS} = 0 V		-	0.79	1.2	V	
Body diode reverse recovery time	t _{rr}				25	50	ns	
Body diode reverse recovery charge	Qrr	1	A -1:/-II - 400 A /	-	16	32	nC	
Reverse recovery fall time	ta	$I_F = 4 P$	A, di/dt = 100 A/μs	-	11	-	ns	
Reverse recovery rise time	t _b	1		-	14	-	ns	
Body diode peak reverse recovery current	I _{RM(REC)}			-	-1.1	-	Α	

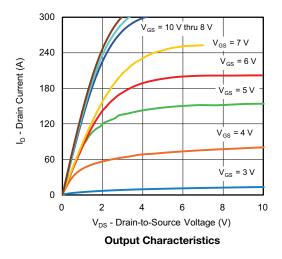
Notes

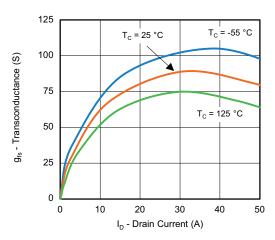
- a. Pulse test; pulse width \leq 300 μ s, duty cycle \leq 2 %
- b. Guaranteed by design, not subject to production testing
- c. Independent of operating temperature

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

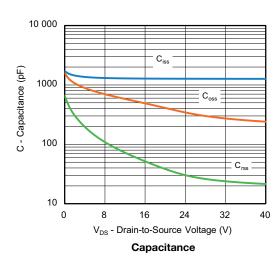


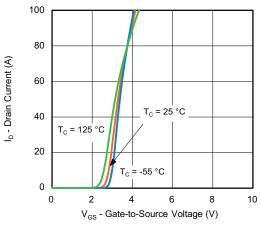
TYPICAL CHARACTERISTICS (T_A = 25 °C, unless otherwise noted)



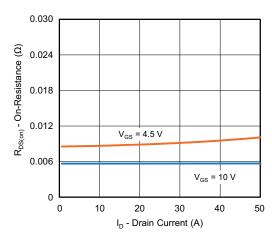


Transconductance

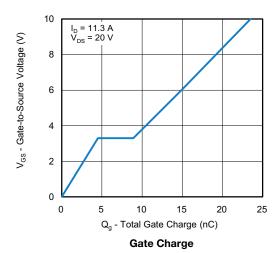






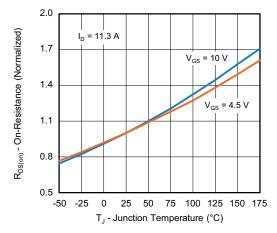


On-Resistance vs. Drain Current

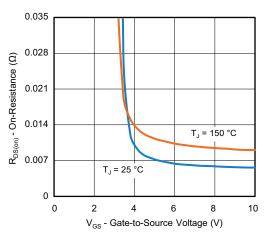




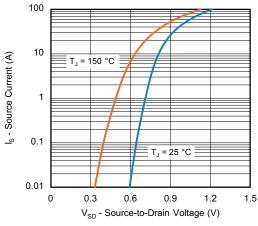
TYPICAL CHARACTERISTICS (T_A = 25 °C, unless otherwise noted)



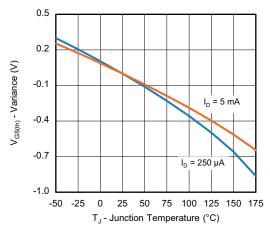
On-Resistance vs. Junction Temperature



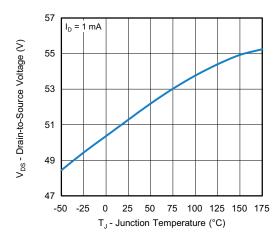
On-Resistance vs. Gate-to-Source Voltage



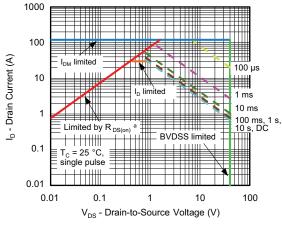
Source Drain Diode Forward Voltage



Threshold Voltage



Drain Source Breakdown vs. Junction Temperature



Safe Operating Area

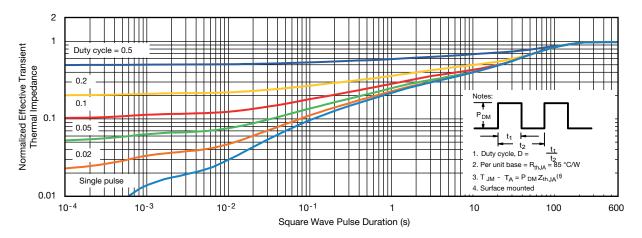
Note

a. V_{GS} > minimum V_{GS} at which R_{DS(on)} is specified

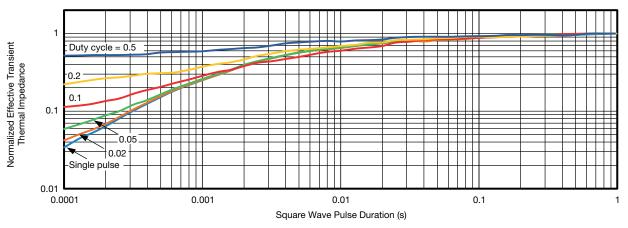
For technical questions, contact: automostech



THERMAL RATINGS (T_A = 25 °C, unless otherwise noted)



Normalized Thermal Transient Impedance, Junction-to-Ambient



Normalized Thermal Transient Impedance, Junction-to-Case

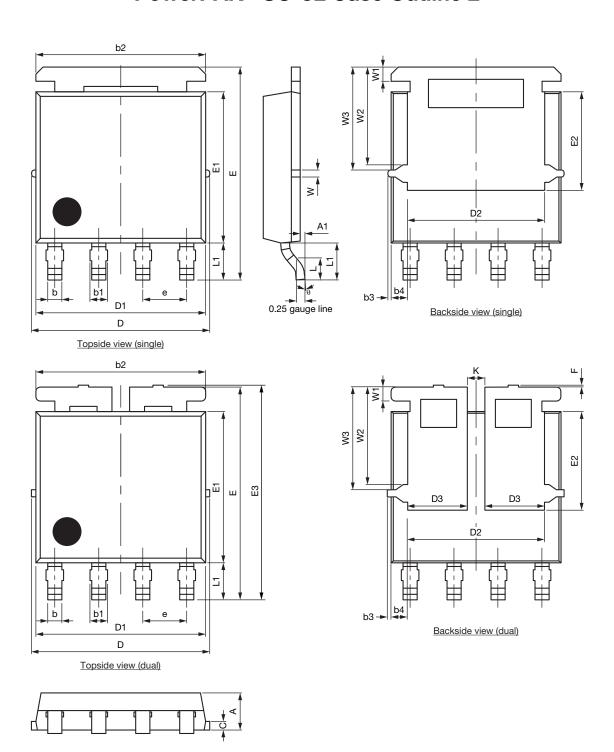
Note

- The characteristics shown in the two graphs
 - Normalized Transient Thermal Impedance Junction-to-Ambient (25 °C)
 - Normalized Transient Thermal Impedance Junction-to-Case (25 °C) are given for general guidelines only to enable the user to get a "ball park" indication of part capabilities. The data are extracted from single pulse transient thermal impedance characteristics which are developed from empirical measurements. The latter is valid for the part mounted on printed circuit board FR4, size 1" x 1" x 0.062", double sided with 2 oz. copper, 100 % on both sides. The part capabilities can widely vary depending on actual application parameters and operating conditions

Vishay Siliconix maintains worldwide manufacturing capability. Products may be manufactured at one of several qualified locations. Reliability data for Silicon Technology and Package Reliability represent a composite of all qualified locations. For related documents such as package / tape drawings, part marking, and reliability data, see www.vishay.com/ppg?77568.



PowerPAK® SO-8L Case Outline 2





www.vishay.com

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DIM	MILLIMETERS			INCHES			
DIM.	MIN.	NOM.	MAX.	MIN.	NOM.	MAX.	
Α	1.00	1.07	1.14	0.039	0.042	0.045	
A1	0.00	-	0.127	0.00	-	0.005	
b	0.33	0.41	0.48	0.013	0.016	0.019	
b1	0.44	0.51	0.58	0.017	0.020	0.023	
b2	4.80	4.90	5.00	0.189	0.193	0.197	
b3	0.094			0.004			
b4		0.47			0.019		
С	0.20	0.25	0.30	0.008	0.010	0.012	
D	5.00	5.13	5.25	0.197	0.202	0.207	
D1	4.80	4.90	5.00	0.189	0.193	0.197	
D2	3.86	3.96	4.06	0.152	0.156	0.160	
D3	1.63	1.73	1.83	0.064	0.068	0.072	
е	1.27 BSC			0.050 BSC			
E	6.05	6.15	6.25	0.238	0.242	0.246	
E1	4.27	4.37	4.47	0.168	0.172	0.176	
E2	2.75	2.85	2.95	0.108	0.112	0.116	
E3	6.05	6.22	6.40	0.238	0.245	0.252	
F	-	-	0.15	-	-	0.006	
L	0.62	0.72	0.82	0.024	0.028	0.032	
L1	0.92	1.07	1.22	0.036	0.042	0.048	
K	0.51				0.020		
W	0.23			0.009			
W1	0.41			0.016			
W2	2.82			0.111			
W3	2.96			0.117			
θ	0°	-	10°	0°	-	10°	

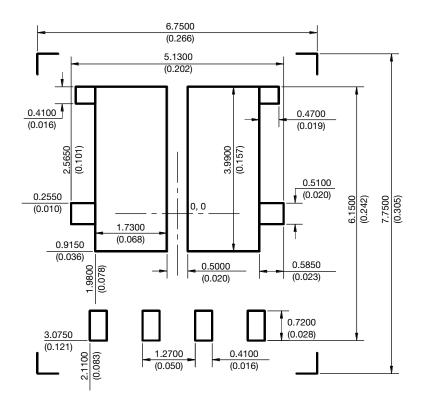
DWG: 6044

Note

• Millimeters will govern



RECOMMENDED MINIMUM PAD FOR PowerPAK® SO-8L DUAL



Recommended Minimum Pads Dimensions in mm (inches) Keep-out 6.75 (0.266) x 7.75 (0.305)



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